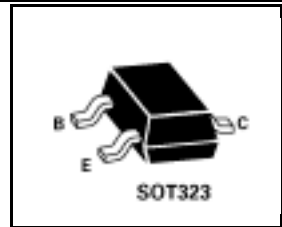


# SOT323 NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ZUMT817-25  
ZUMT817-40

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PARTMARKING DETAILS	ZUMT817-25 - T7
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COMPLEMENTARY TYPES	ZUMT817-25 - ZUMT807-25
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## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	50	V
Collector-Emitter Voltage	$V_{CEO}$	45	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Peak Pulse Current	$I_{CM}$	1	A
Continuous Collector Current	$I_C$	500	mA
Base Current	$I_B$	100	mA
Peak Base Current	$I_{BM}$	200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector Cut-Off Current	$I_{CBO}$			0.1 5	$\mu A$ $\mu A$	$V_{CB}=20V, I_E=0$ $V_{CB}=20V, I_E=0, T_{amb}=150^{\circ}C$
Emitter Cut-Off Current	$I_{EBO}$			10	$\mu A$	$V_{EB}=5V, I_C=0$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			700	mV	$I_C=500mA, I_B=50mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$			1.2	V	$I_C=500mA, V_{CE}=1V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100		600		$I_C=100mA, V_{CE}=1V^*$ $I_C=500mA, V_{CE}=1V^*$
		40				
		-25	160	400		$I_C=100mA, V_{CE}=1V^*$
		-40	250	600		$I_C=100mA, V_{CE}=1V^*$
Transition Frequency	$f_T$		200		MHz	$I_C=10mA, V_{CE}=5V$ $f=35MHz$
Collector-base Capacitance	$C_{obo}$		5.0		pF	$I_E=I_C=0, V_{CB}=10V$ $f=1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$